

# P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)	
- 100	$0.195$ at $V_{GS} = -10 \text{ V}$	- 19	11.7	
- 100	0.210 at V <sub>GS</sub> = - 4.5 V	- 17	11.7	

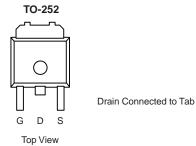
#### **FEATURES**

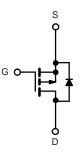
- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
   Compliant to RoHS Directive 2002/95/EC



#### **APPLICATIONS**

- · Power Switch
- DC/DC Converters





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T <sub>C</sub> = 25 °C, unless oth	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	- 100	V		
Gate-Source Voltage		V <sub>GS</sub>	± 20	¬	
Continuous Proin Current /T = 150 °C\	T <sub>C</sub> = 25 °C	I-	- 19		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	- 12.1		
Pulsed Drain Current		I <sub>DM</sub>	- 57	_ A	
Avalanche Current		I <sub>AS</sub>	- 18		
ingle Avalanche Energy <sup>a</sup> L = 0.1 mH		E <sub>AS</sub>	16.2	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	32.1 <sup>b</sup>	· W	
	T <sub>A</sub> = 25 °C <sup>c</sup>	$ P_D$ $-$	2.5		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	50	°C/W	
Junction-to-Case (Drain)	R <sub>thJC</sub>	3.9		

#### Notes:

- a. Duty cycle ≤ 1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).



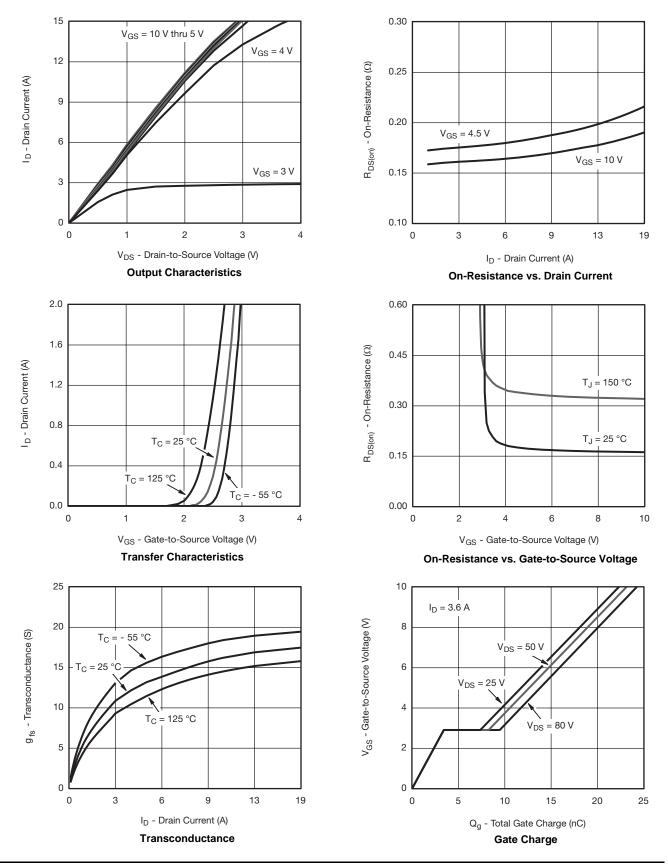
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 100			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 2.5		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
		V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50		
		V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α	
	В	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3.6 A		0.162	0.195	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.4 A		0.175	0.210		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 3.6 A		12		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = - 50 V, f = 1 MHz		1055		pF	
Output Capacitance	C <sub>oss</sub>			65			
Reverse Transfer Capacitance	C <sub>rss</sub>			41			
	Qg	$V_{DS} = -50 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3.6 \text{ A}$		23.2	34.8	nC	
Total Gate Charge <sup>c</sup>		V <sub>DS</sub> = -50 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.6 A		11.7	17.6		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			3.5			
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			4.8			
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1.2	5.7	11.5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			7	14		
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> = - 50 V, R <sub>L</sub> = 17.2 Ω		12	18	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			33	50		
Fall Time <sup>c</sup>	t <sub>f</sub>	]		9	18		
Drain-Source Body Diode Ratings at	nd Characteri	stics T <sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	I <sub>S</sub>				- 19	Τ.	
Pulsed Current	I <sub>SM</sub>				- 57	A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 2.9 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			50	75	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = - 2.9 A, dl/dt = 100 A/μs		- 4	- 6	Α	
Reverse Recovery Charge	Q <sub>rr</sub>	†		98	147	nC	

#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.c. Independent of operating temperature.

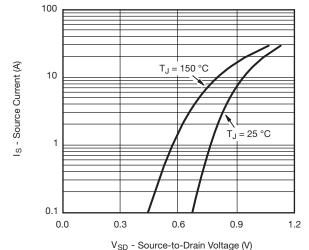
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

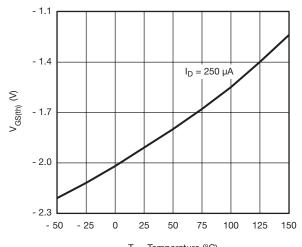




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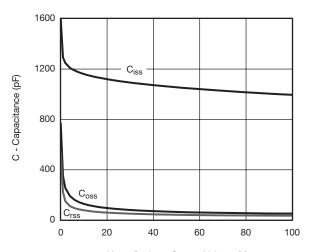


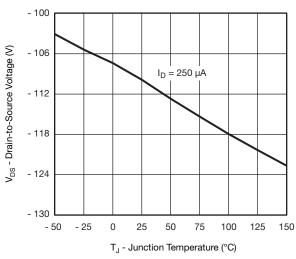
Source-Drain Diode Forward Voltage



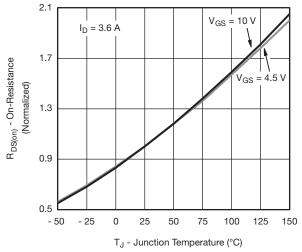
T<sub>J</sub> - Temperature (°C)

Threshold Voltage

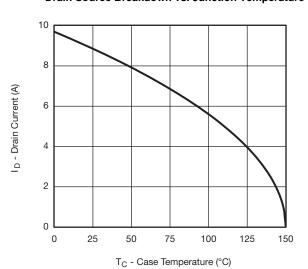




**Drain Source Breakdown vs. Junction Temperature** 



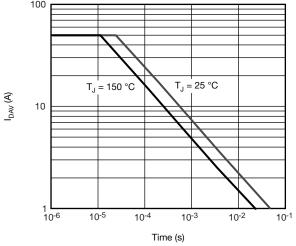
On-Resistance vs. Junction Temperature



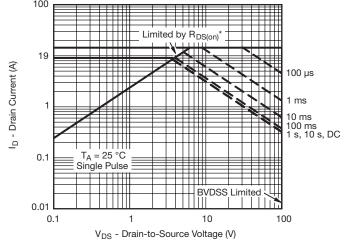
**Current Derating** 



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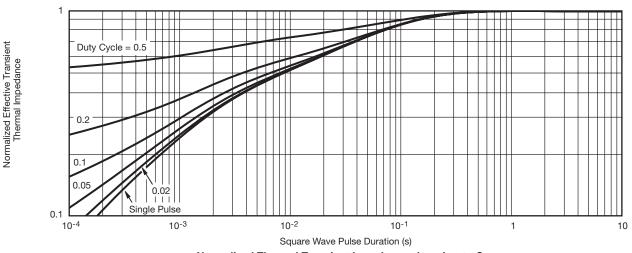


Single Pulse Avalanche Current Capability vs. Time



 $^{\star}$  V  $_{GS}$  > minimum V  $_{GS}$  at which R  $_{DS(on)}$  is specified

#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



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